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N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A)	Q _g (Typ.)			
40	1 at V _{GS} = 10 V	300	340 nC			
40	1.3 at V _{GS} = 4.5 V	300				

FEATURES

- DT-Trench Power MOSFET
- 100 % R_q and UIS tested
- Very low on-resistance
- 175 °C Junction Temperature



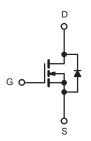
APPLICATIONS

- DC/DC Converter
- Synchronous Rectification in DC/DC and AC/DC Converters



TO-263 Pin Configuration

Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	40	V			
Gate-Source Voltage	V _{GS}	± 20	V			
O a tito a a D a i a O a a a t T = 175 00/3	T _C = 25 °C		300	A		
Continuous Drain Current (T _J = 175 °C) ^a	T _C = 100 °C	I _D	195			
Pulsed Drain Current ^b	I _{DM}	900				
Single Avalanche Energy	E _{AS}	1500	mJ			
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	275 ^a	W		
waxiinum rowei bissipation	T _C = 100 °C	FD	137			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount)d	t ≤ 10 s	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	Steady State	R _{thJC}	0.55	C/VV		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_D=250\;\mu A$	1	-	3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
Zero Gate Voltage Drain Gurrent	I _{DSS}	V_{DS} = 36 V, V_{GS} = 0 V, T_J = 125 °C	-	-	100	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	300	-	-	Α
Drain-Source On-State Resistance a	D	V _{GS} = 10 V, I _D = 20 A -		1	1.3	0
Dialii-Source Oil-State nesistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 20 A	-	1.3	1.7	mΩ
Forward Transconductance ^a	rward Transconductance ^a g_{fs} $V_{DS} = 5 \text{ V}, I_D = 20 \text{ A}$		-	85	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	16700	=	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	1300	=	
Reverse Transfer Capacitance	C _{rss}		-	1500	-	
Total Gate Charge ^c	Q_g			340	-	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	33	=	nC
Gate-Drain Charge ^c	Q _{gd}		-	58	-	
Gate Resistance	R_g	f = 1 MHz	-	1.6	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	16	-	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, I_D = 20 \text{ A}, R_g = 2.5 \Omega$	-	18	=	ns
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	110	-	
Fall Time ^c	t _f		-	30	-	
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	300	Α
Pulsed Current	I _{SM}		-	-	900	Α
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}	L = 20 A di/dt = 100 A/::=	-	30	-	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	155	-	nC

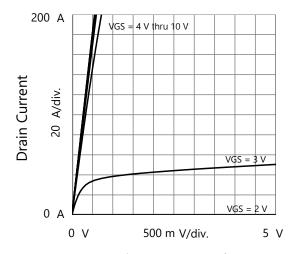
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

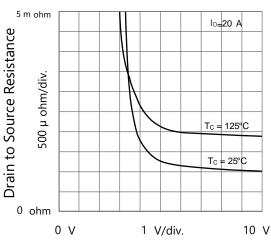
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



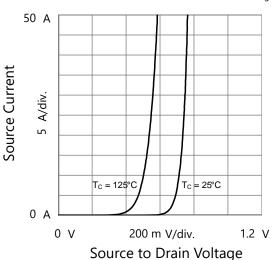
TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



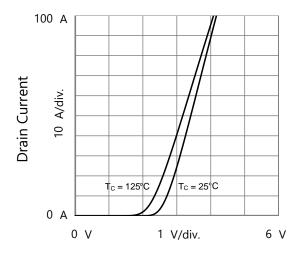
Drain to Source Voltage Output Characteristics



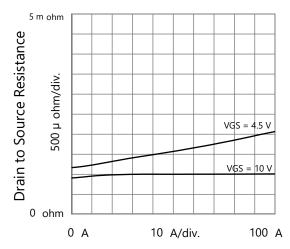
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



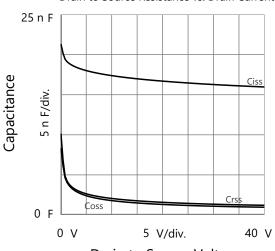
Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics

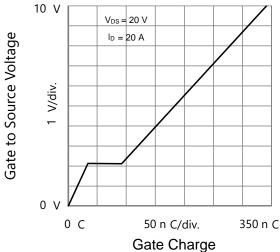


Drain Current
Drain to Source Resistance vs. Drain Current

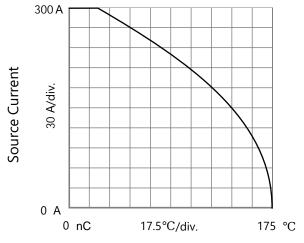




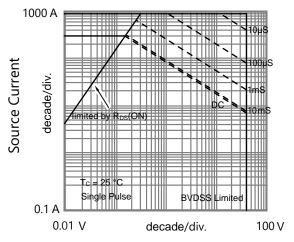
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



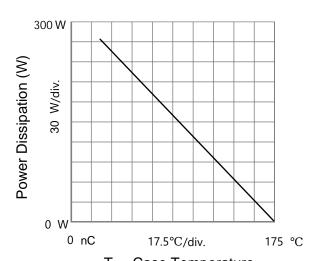
Gate Charge
Gate to Source Voltage vs. GateCharge



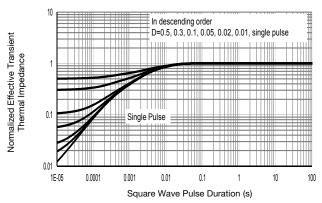
T_C - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



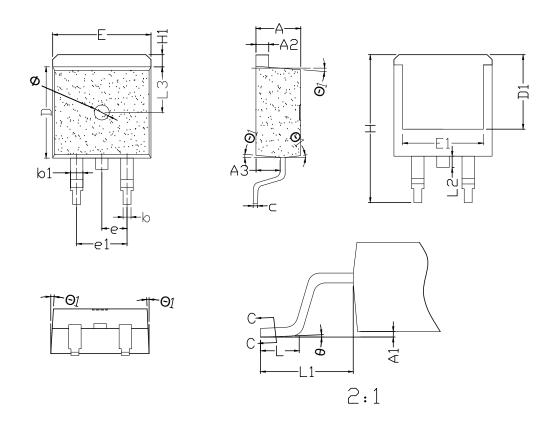
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



TO-263 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
Α	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1	7.50REF			ф	0°	2°	5°
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ	1.5BSC		





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